

NTJD3158C

Power MOSFET

20 V, +0.63/-0.82 A,
SC-88 Complementary, ESD Protected

Features

- Complementary N- and P-Channel MOSFET
- Small Size Dual SC-88 Package
- Reduced Gate Charge to Improve Switching Response
- Independently Connected Devices to Provide Design Flexibility
- This is a Pb-Free Device

Applications

- DC-DC Conversion Circuits
- Load/Power Switching with Level Shift

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V _{DSS}	20	V	
Gate-to-Source Voltage		V _{GS}	±12	V	
N-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	0.63	A
		T _A = 85°C		0.46	
	t ≤ 5 s	T _A = 25°C		0.72	
P-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	-0.82	A
		T _A = 85°C		-0.59	
	t ≤ 5 s	T _A = 25°C		-0.93	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	0.27	W
	t ≤ 5 s			0.35	
Pulsed Drain Current	N-Ch	tp = 10 μs	I _{DM}	1.3	A
	P-Ch			-1.6	
Operating Junction and Storage Temperature		T _J , T _{stg}	-55 to 150	°C	
Source Current (Body Diode)		I _S	0.46	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	R _{θJA}	460	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 1)	R _{θJA}	357	
Junction-to-Lead (Drain) – Steady State (Note 1)	R _{θJL}	226	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

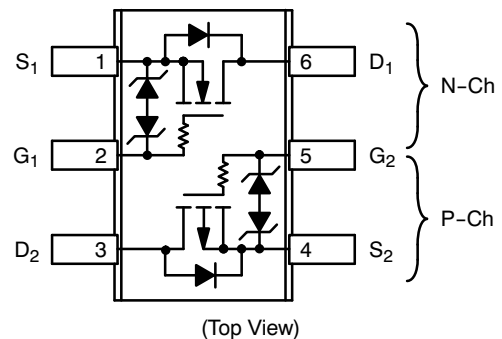


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V _{(BR)DSS}	R _{DS(on)} Max	I _D Max
N-Ch 20 V	375 mΩ @ 4.5 V	0.63 A
	445 mΩ @ 2.5 V	
P-Ch -20 V	300 mΩ @ -4.5 V	-0.82 A
	500 mΩ @ -2.5 V	

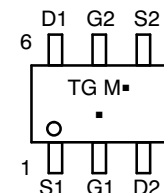
SC-88 (SOT-363) (6-Leads)



MARKING DIAGRAM & PIN ASSIGNMENT



SC-88 (SOT-363)
CASE 419B
STYLE 26



- TG = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTJD3158CT1G	SC-88 (Pb-Free)	3000/Tape & Reel
NTJD3158CT4G	SC-88 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS (Note 3)							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	N	V _{GS} = 0 V	I _D = 250 μA	20		V
		P		I _D = -250 μA	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				22		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	N	V _{GS} = 0 V, V _{DS} = 16 V			1.0	μA
		P	V _{GS} = 0 V, V _{DS} = -16 V			1.0	
Gate-to-Source Leakage Current	I _{GSS}	N	V _{DS} = 0 V, V _{GS} = ±12 V			±10	μA
		P	V _{DS} = 0 V, V _{GS} = ±4.5 V			±1.0	
		P	V _{DS} = 0 V, V _{GS} = ±12 V		6.0		

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	N	I _D = 250 μA	0.6		1.5	V
		P	I _D = -250 μA	-0.45			
Drain-to-Source On Resistance	R _{DS(on)}	N	V _{GS} = 4.5 V, I _D = 0.63 A		290	375	mΩ
		P	V _{GS} = -4.5 V, I _D = -0.88 A		255	300	
		N	V _{GS} = 2.5 V, I _D = 0.40 A		360	445	
		P	V _{GS} = -2.5 V, I _D = -0.71 A		345	500	
Forward Transconductance	g _{FS}	N	V _{DS} = 4.0 V, I _D = 0.63 A		2.0		S
		P	V _{DS} = -10 V, I _D = -0.88 A		3.0		

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	N	f = 1 MHz, V _{GS} = 0 V	V _{DS} = 20 V		33	46	pF	
		P		V _{DS} = -20 V		155			
Output Capacitance	C _{OSS}	N		V _{DS} = 20 V		13	22		
		P		V _{DS} = -20 V		25			
Reverse Transfer Capacitance	C _{RSS}	N		V _{DS} = 20 V		2.8	5.0		
		P		V _{DS} = -20 V		18			
Total Gate Charge	Q _{G(TOT)}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		1.3	3.0		nC
		P		V _{GS} = -4.5 V, V _{DS} = -15 V, I _D = -0.88 A		2.2			
Gate-to-Source Charge	Q _{GS}	N		V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		0.2			
		P		V _{GS} = -4.5 V, V _{DS} = -15 V, I _D = -0.88 A		0.5			
Gate-to-Drain Charge	Q _{GD}	N	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 0.63 A		0.4				
		P	V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		0.65				

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	N	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 0.5 A, R _G = 20 Ω		83		ns	
Rise Time	t _r				227			
Turn-Off Delay Time	t _{d(OFF)}				786			
Fall Time	t _f				506			
Turn-On Delay Time	t _{d(ON)}	P		V _{GS} = -4.5 V, V _{DD} = -10 V, I _D = -0.5 A, R _G = 20 Ω		5.8		
Rise Time	t _r					6.5		
Turn-Off Delay Time	t _{d(OFF)}					13.5		
Fall Time	t _f					3.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	N	V _{GS} = 0 V, T _J = 25°C	I _S = 0.23 A	0.76	1.1	V
		P		I _S = -0.48 A	-0.8	-1.2	
		N	V _{GS} = 0 V, T _J = 125°C	I _S = 0.23 A	0.63		
		P		I _S = -0.48 A	-0.66		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES (N-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

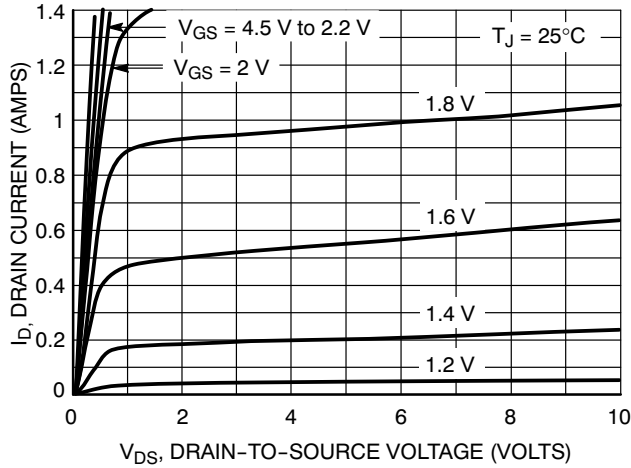


Figure 1. On-Region Characteristics

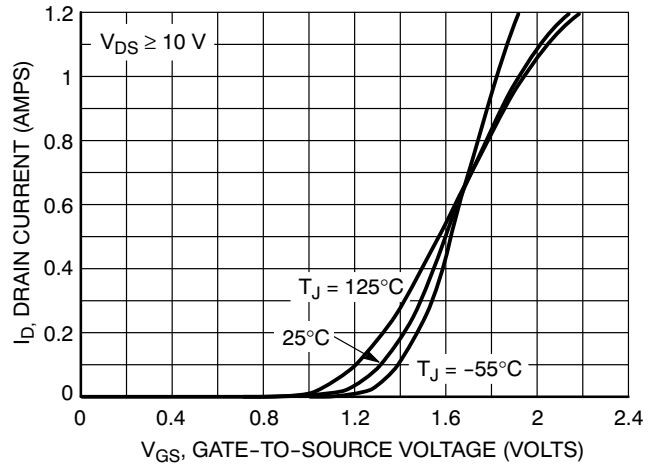


Figure 2. Transfer Characteristics

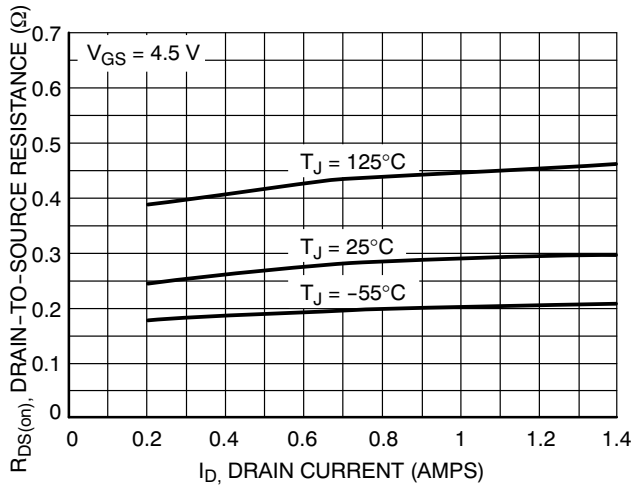


Figure 3. On-Resistance vs. Drain Current and Temperature

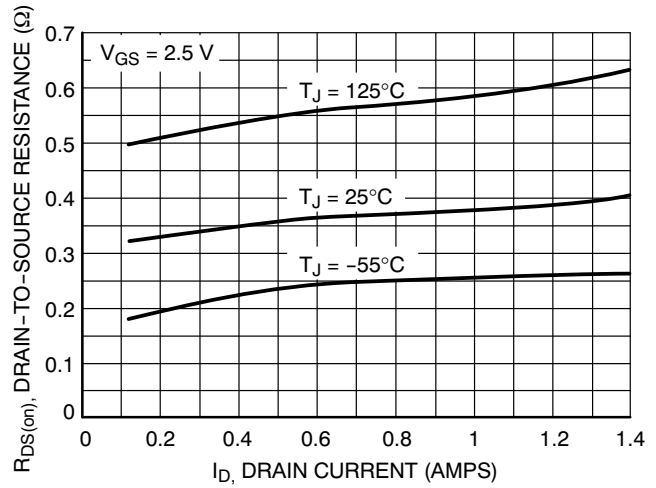


Figure 4. On-Resistance vs. Drain Current and Temperature

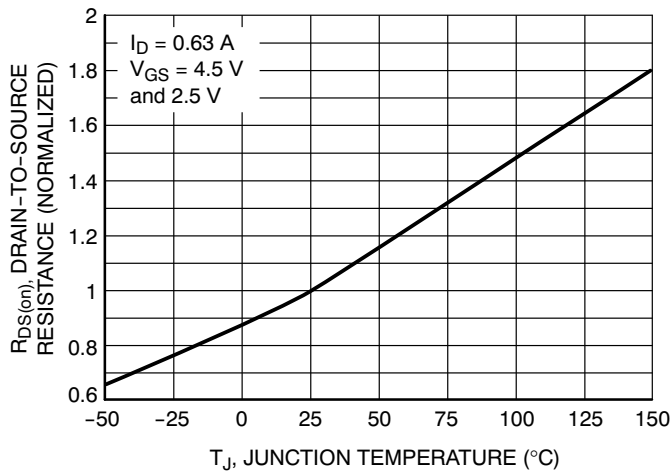


Figure 5. On-Resistance Variation with Temperature

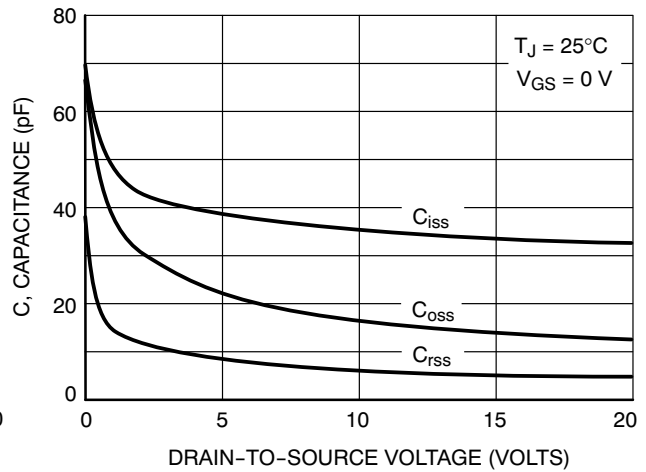


Figure 6. Capacitance Variation

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TYPICAL PERFORMANCE CURVES (N-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

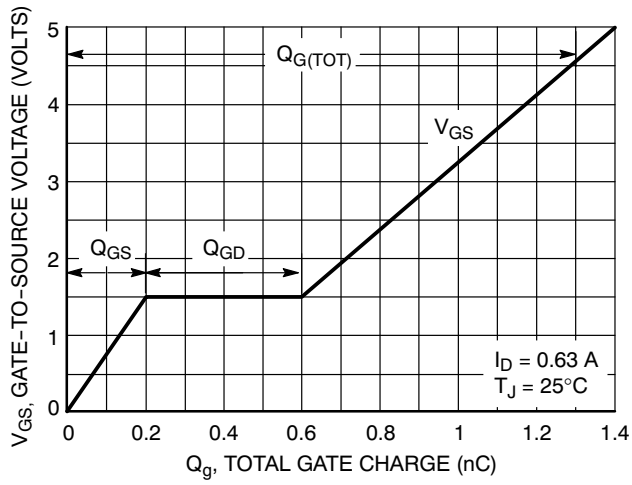


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

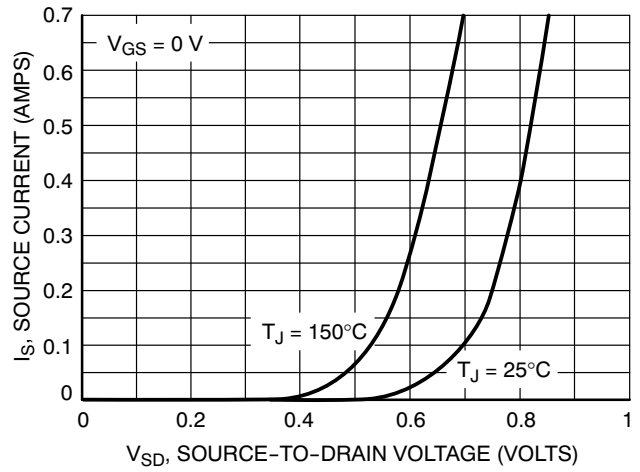


Figure 8. Diode Forward Voltage vs. Current

TYPICAL PERFORMANCE CURVES (P-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

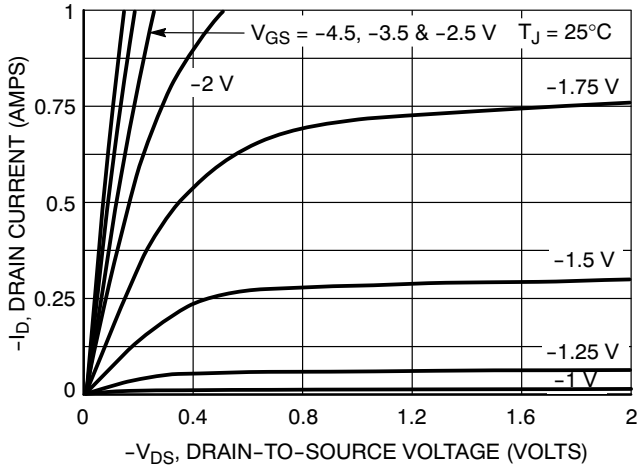


Figure 9. On-Region Characteristics

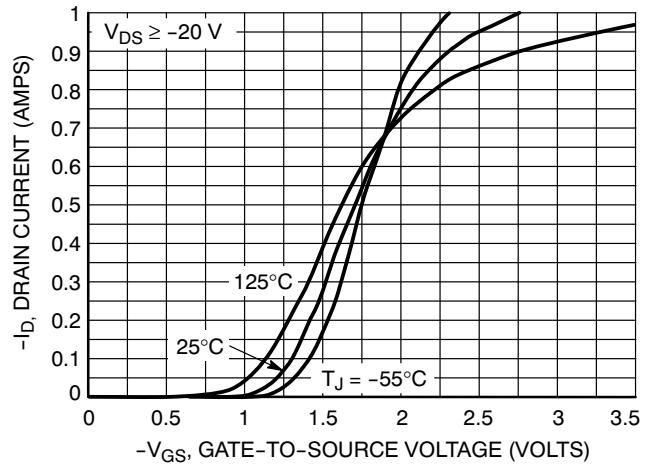


Figure 10. Transfer Characteristics

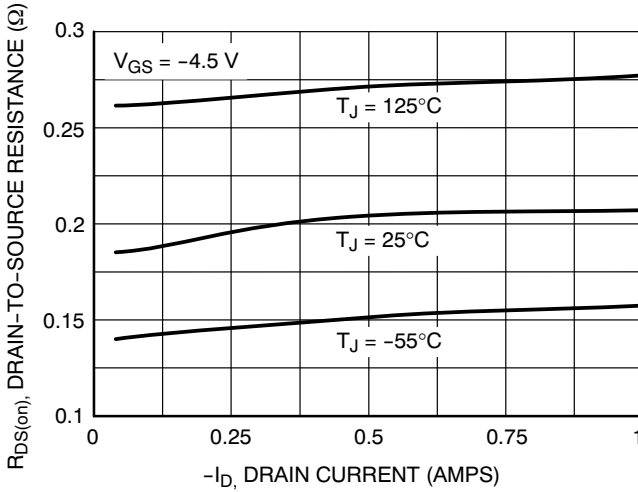


Figure 11. On-Resistance vs. Drain Current and Temperature

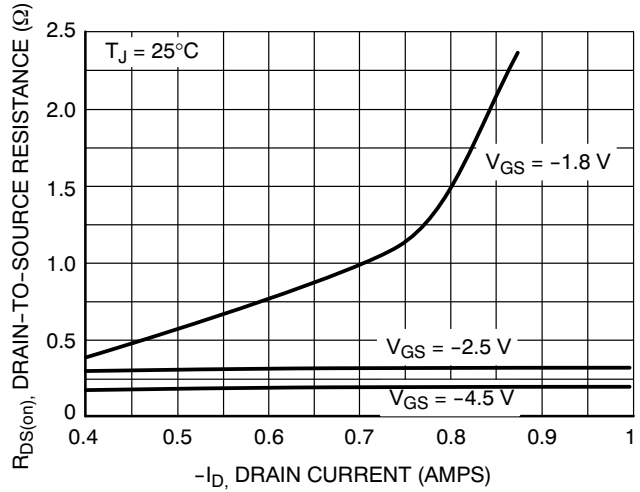


Figure 12. On-Resistance vs. Drain Current and Gate Voltage

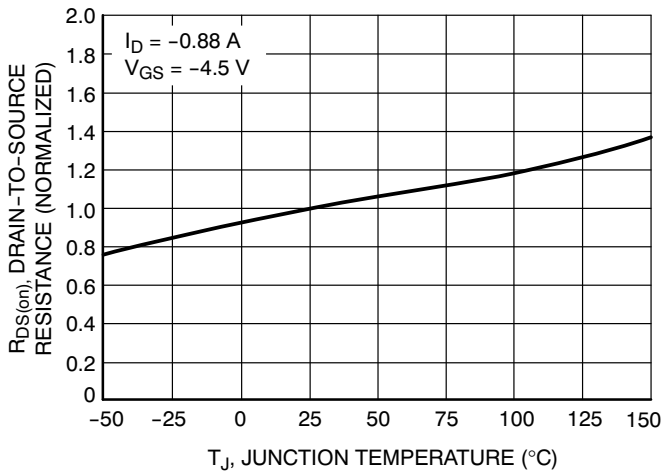


Figure 13. On-Resistance Variation with Temperature

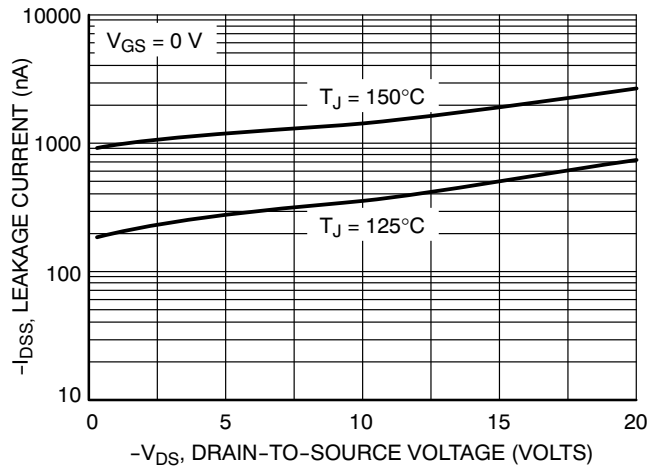


Figure 14. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES (P-Ch) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

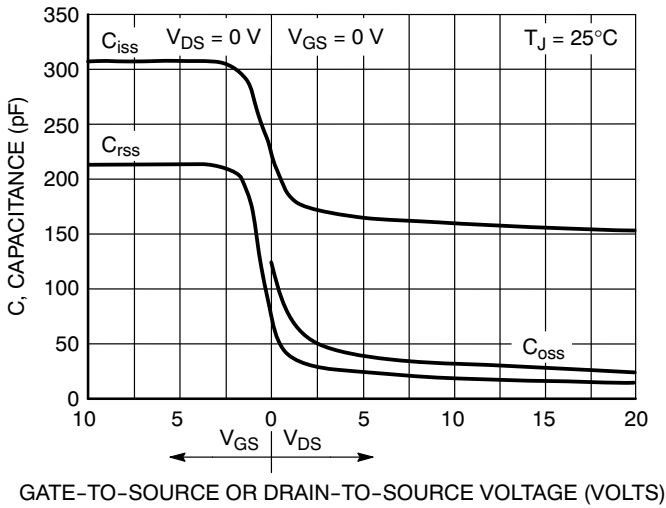


Figure 15. Capacitance Variation

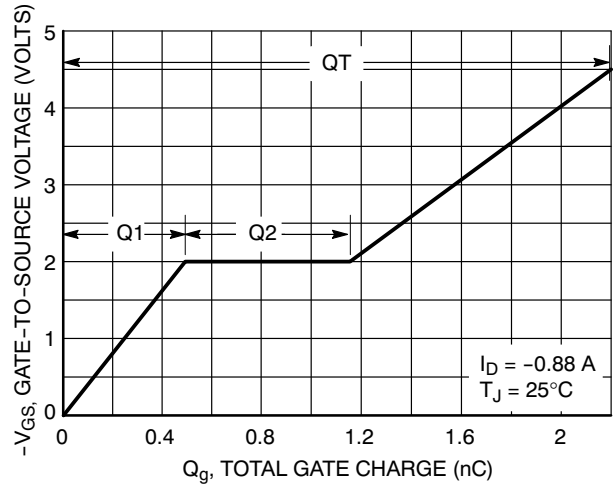


Figure 16. Gate-to-Source Voltage vs. Total Gate Charge

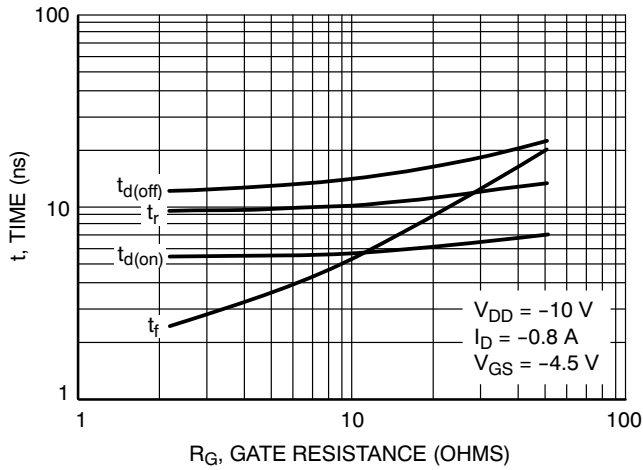


Figure 17. Resistive Switching Time Variation vs. Gate Resistance

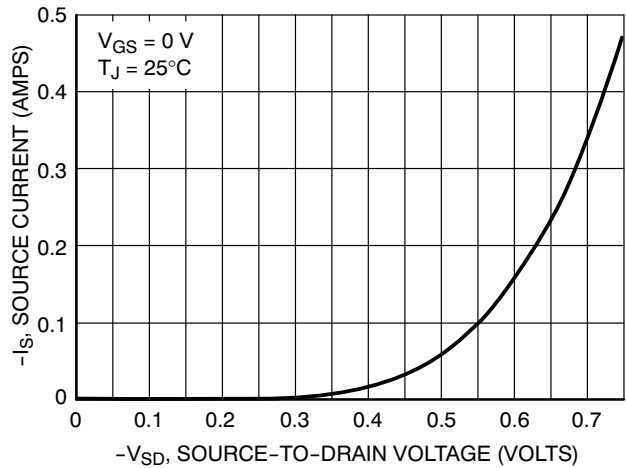


Figure 18. Diode Forward Voltage vs. Current

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

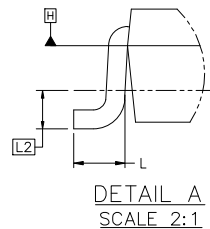
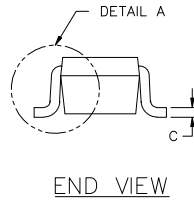
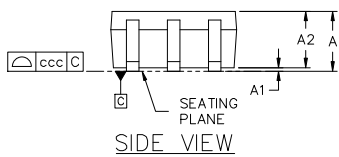
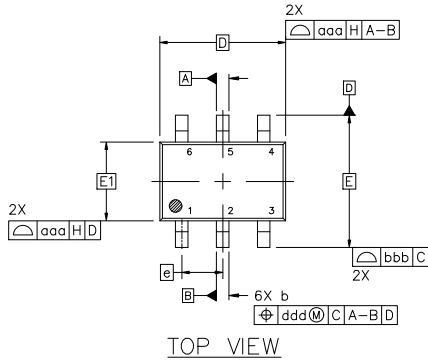


SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

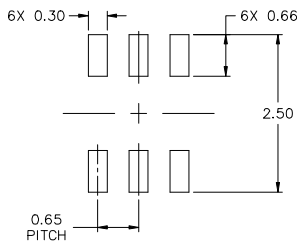
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

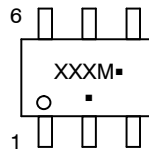


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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